

IR2308(S) & (PbF)

HALF-BRIDGE DRIVER

Features

- Floating channel designed for bootstrap operation Fully operational to +600V Tolerant to negative transient voltage dV/dt immune
- Gate drive supply range from 10 to 20V
- Undervoltage lockout for both channels
- 3.3V, 5V and 15V input logic compatible
- Cross-conduction prevention logic
- Matched propagation delay for both channels
- Outputs in phase with inputs
- Logic and power ground +/- 5V offset.
- Internal 540ns dead-time
- Lower di/dt gate driver for better noise immunity
- Also available LEAD_FREE

Description

The IR2308(S) are high voltage, high speed power MOSFET and IGBT drivers with dependent high and low side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. The logic input is

Packages

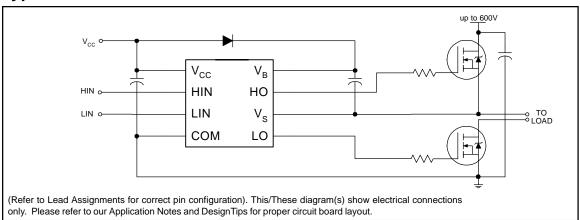


2106//2108//2109/2304/2308 Feature Comparison

Part	Input logic	Cross- conduction prevention logic	Dead-Time	Ground Pins	
2106	HIN/LIN	no	none	СОМ	
21064	HIIV/LIIV	no	none	VSS/COM	
2108	HIN/LIN	yes	Internal 540ns	COM	
21084	I IIIN/LIIN	yes	Programmable 0.54~5 μs	VSS/COM	
2109	IN/SD	yes	Internal 540ns	СОМ	
21094	IIV/SD	Programmable 0.54~5 μs V		VSS/COM	
2304	HIN/LIN	yes	Internal 100ns	СОМ	
2308	HIN/LIN	yes	Internal 540ns	COM	

compatible with standard CMOS or LSTTL output, down to 3.3V logic. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side configuration which operates up to 600 volts.

Typical Connection



Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Min.	Max.	Units	
V _B	High side floating absolute voltage		-0.3	625	
Vs	High side floating supply offset voltage		V _B - 25	V _B + 0.3	
V _{HO}	High side floating output voltage		V _S - 0.3	V _B + 0.3	V
Vcc	Low side and logic fixed supply voltage		-0.3	25	V
VLO	Low side output voltage		-0.3	V _{CC} + 0.3	
V_{IN}	Logic input voltage (HIN & LIN)		V _{SS} - 0.3	V _{CC} + 0.3	
dV _S /dt	Allowable offset supply voltage transient		_	50	V/ns
PD	Package power dissipation @ T _A ≤ +25°C	(8 lead PDIP)	_	1.0	147
		(8 lead SOIC)	_	0.625	W
RthJA	Thermal resistance, junction to ambient	(8 lead PDIP)	_	125	°C/W
		(8 lead SOIC)	_	200	0,11
T_J	Junction temperature		_	150	
T _S	Storage temperature		-50	150	°C
TL	Lead temperature (soldering, 10 seconds)		_	300	

Recommended Operating Conditions

The Input/Output logic timing diagram is shown in figure 1. For proper operation the device should be used within the recommended conditions. The V_S and V_{SS} offset rating are tested with all supplies biased at 15V differential.

Symbol	Definition	Min.	Max.	Units
VB	High side floating supply absolute voltage	V _S + 10	V _S + 20	
Vs	High side floating supply offset voltage	Note 1	600	
V _{HO}	High side floating output voltage	٧s	V _B	V
Vcc	Low side and logic fixed supply voltage	10	20	
VLO	Low side output voltage	0	Vcc	
V _{IN}	Logic input voltage	COM	V _{CC}	
T _A	Ambient temperature	-40	125	°C

Note 1: Logic operational for V_S of -5 to +600V. Logic state held for V_S of -5V to -V_{BS}. (Please refer to the Design Tin DT97-3 for more details).

Dynamic Electrical Characteristics

 V_{BIAS} (V_{CC}, V_{BS}) = 15V, V_{SS} = COM, C_L = 1000 pF, T_A = 25°C, DT = VSS unless otherwise specified.

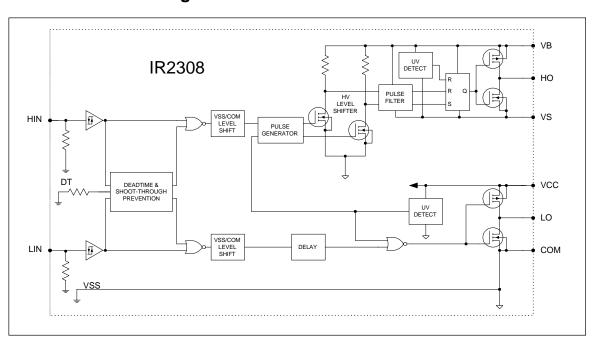
Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
ton	Turn-on propagation delay	_	220	300		Vs = 0V
toff	Turn-off propagation delay	_	200	280		V _S = 0V or 600V
MT	Delay matching ton - toff	_	0	46		
t _r	Turn-on rise time	_	150	220		V _S = 0V
tf	Turn-off fall time	_	50	80	nsec	V _S = 0V
DT	Deadtime: LO turn-off to HO turn-on(DTLO-HO) &	400	540	680		
	HO turn-off to LO turn-on (DTHO-LO)					
MDT	Deadtime matching = DTLO-HO - DTHO-LO	_	0	60		

Static Electrical Characteristics

 V_{BIAS} (V_{CC} , V_{BS}) = 15V, V_{SS} = COM, DT= V_{SS} and T_A = 25°C unless otherwise specified. The V_{IL} , V_{IH} and I_{IN} parameters are referenced to V_{SS} /COM and are applicable to the respective input leads: HIN and LIN. The V_O , I_O and Ron parameters are referenced to COM and are applicable to the respective output leads: HO and LO.

Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
V _{IH}	Logic "1" input voltage for HIN & LIN	2.9	_	_		V _{CC} = 10V to 20V
V _{IL}	Logic "0" input voltage for HIN & LIN	_	_	0.8	V	V _{CC} = 10V to 20V
V _{OH}	High level output voltage, V _{BIAS} - V _O	_	0.8	1.4	\ \ \	I _O = 20 mA
V _{OL}	Low level output voltage, VO	_	0.3	0.6		I _O = 20 mA
I _{LK}	Offset supply leakage current	_	_	50	_	V _B = V _S = 600V
I _{QBS}	Quiescent V _{BS} supply current	20	60	150	μA	V _{IN} = 0V or 5V
IQCC	Quiescent V _{CC} supply current	0.4	1.0	1.6	mA	V _{IN} = 0V or 5V
I _{IN+}	Logic "1" input bias current	_	5	20		HIN = 5V, LIN = 5V
I _{IN-}	Logic "0" input bias current	_	1	2	μA	HIN = 0V, LIN = 0V
V _{CCUV+}	V _{CC} and V _{BS} supply undervoltage positive going	8.0	8.9	10		
V _{BSUV+}	threshold					
V _{CCUV} -	V _{CC} and V _{BS} supply undervoltage negative going	7.4	8.2	9.0	V	
V _{BSUV} -	threshold					
VCCUVH	Hysteresis	0.3	0.7	_		
V _{BSUVH}						
I _{O+}	Output high short circuit pulsed current	97	200	_		$V_O = 0V$,
					mA	PW ≤ 10 µs
I _O -	Output low short circuit pulsed current	250	350	-	'''^	$V_0 = 15V$,
						PW ≤ 10 μs

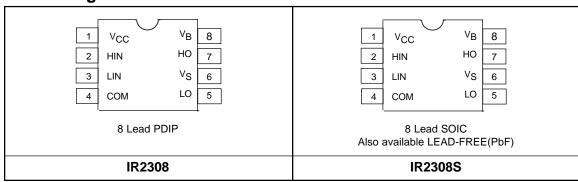
Functional Block Diagram



Lead Definitions

Symbol	Description
HIN	Logic input for high side gate driver output (HO), in phase
LIN	Logic input for low side gate driver output (LO), in phase
V _B	High side floating supply
НО	High side gate driver output
٧s	High side floating supply return
Vcc	Low side and logic fixed supply
LO	Low side gate driver output
СОМ	Low side return

Lead Assignments



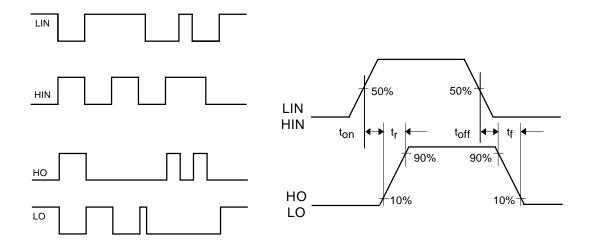


Figure 1. Input/Output Timing Diagram

Figure 2. Switching Time Waveform Definitions

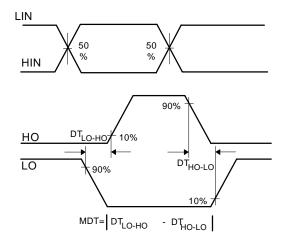


Figure 3. Deadtime Waveform Definitions

International

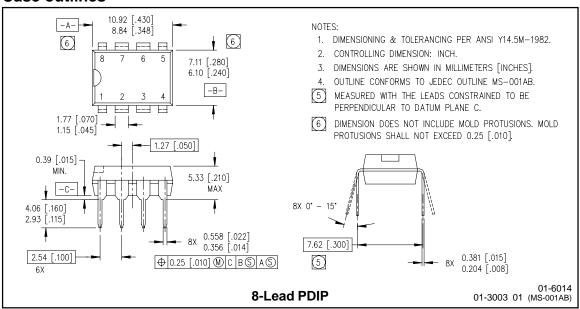
IOR Rectifier

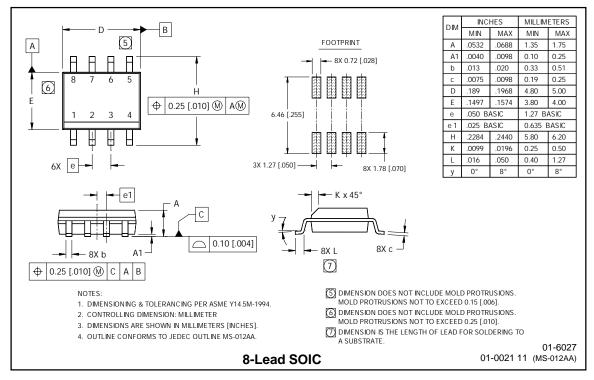
IR WORLD HEADQUARTERS: 233 Kansas Street, El Segundo, California 90245 Tel: (310) 252-7105

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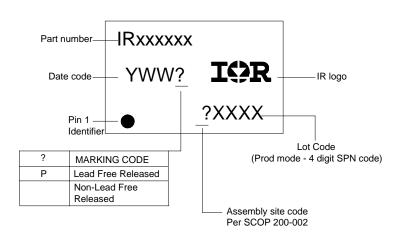
IR2308(S) & (PbF)

Case outlines





LEADFREE PART MARKING INFORMATION



ORDER INFORMATION

Basic Part (Non-Lead Free)

8-Lead PDIP IR2308 order IR2308 8-Lead SOIC IR2308S order IR2308S

Leadfree Part

8-Lead PDIP R2308 not available 8-Lead SOIC IR2308S order IR2308SPbF

International TOR Rectifier

Thisproduct has been designed and qualified for the industrial market.

Qualification Standards can be found on IR's Web Site http://www.irf.com

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